

# High sensitive photodiodes



### **General Description**

The epc3xx family products are high-sensitive photo diodes for light-barrier, light-curtain, and the like applications. These photo diodes are designed to be used in a reverse-bias mode.

This device allows the design of short to long range light barriers from a few millimeters up to tens of meters.

Using chips from the epc3xx product line, linear or two dimensional arrays can be formed for any application, be it triangulation, spot location, angle measurement, rotary encoders, or similar. Also, spectral sensitive detectors can easily be designed by applying color filters in front of the photo diodes.

Also, other mechanical dimensions are available upon request. It is be possible to manufacture photo diodes of up to 15x15 mm or even bigger. Such a 15x15 mm device then would contain 450 individual photo diodes, each of them individually accessible. All diodes feature a very high quantum efficiency of 90% in the near IR range, a reverse breakdown voltage of up to 30 Volts and a response time down to less than 100ns. All devices are available upon request with optical bandpass filters.

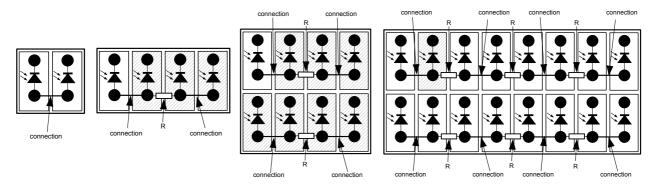
### **Features**

- Low dark current
- High quantum efficiency
- High dynamic range
- Diodes can be used in parallel
- CSP package with very small footprint
- Near infrared and visible version available
- Customer specific wavelength filter upon request

# **Applications**

- Light barriers ranging from millimeters to tens of meters
- Light curtains
- Smoke detectors
- Liquid detectors
- Heart beat monitors
- Position detection (rotary, linear, angle, etc.)
- IR remote control of Hi-Fi, TV sets and other equipment
- Leveling instruments
- Differential measurement
- Linear photo diode arrays

## **Product Range Overview**



R: refer to chapter "Electrical isolation between individual diodes"

Model	No. of Photo Diodes	Diode Length (mm)	Diode Width (mm)	Total Active Area (mm²)	Typ. Dark Current at 20°C (pA )	Ideal Bias Voltage (V)	Wavelength (nm)	Footprint
Single diode	1	1.0	0.5	0.43	20	5	400 - 1050	
epc300	2	1.0	1.0	0.86	40	5	400 - 1050	CSP4
epc310	4	2.0	1.0	1.71	80	5	400 - 1050	CSP8
epc320	8	2.0	2.0	3.42	160	5	400 - 1050	CSP16
epc330	16	4.0	2.0	6.84	320	5	400 - 1050	CSP32

Type specific characteristics (all diodes of the array connected in parallel)



Absolute Maximum Ratings	Recommended Operating Conditions				
Reverse Voltage V <sub>R</sub>	30.0 V		Min.	Max.	Units
Breakdown Voltage between Diodes	10.0 V	Reverse Voltage (V <sub>R</sub> )	1.5	20.0	V
Storage Temperature Range (T <sub>s</sub> )	-40°C to +85°C	Operating Temperature (T <sub>A</sub> )	-40	+85	°C
Lead Temperature solder, 4 sec. (T <sub>L</sub> )	+260°C	Relative Humidity (non-condensing)	+5	+95	%

**Note 1:** Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Recommended operating conditions indicate conditions for which the device is intended to be functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see Electrical Characteristics.

**Note 2:** This device is a highly sensitive CMOS photodiodes with an ESD rating of JEDEC HBM class 2 (<2kV). Handling and assembly of this device should only be done at ESD protected workstations.

Note 3: Unless otherwise stated, measuring parameters are  $V_R = 5.0 \text{ V}$ , -40°C <  $T_A < +85$ °C,  $R_L = 50 \Omega$ 

Note 4: Unless otherwise stated, measurement data apply for individual photo diodes in multi diode chips

### **General Characteristics** (Notes 3, 4)

Symbol	Parameter	Conditions/Comments		Values		
			Min.	Тур.	Max.	
$\lambda_{\text{S max.}}$	Wavelength	max. Sensitivity		850		nm
λ	Wavelength Range	S = 20 % of S <sub>max</sub>	400		1030	nm
S <sub>λ</sub>	Spectral Sensitivity	$\lambda$ = 850nm, $V_R$ = 5V, $I_e$ = 1 mW/cm <sup>2</sup> , type epc300		0.6		A/W
η	Quantum Efficiency	$\lambda$ = 850nm, $V_R$ = 5V, $I_e$ = 1 mW/cm <sup>2</sup> , type epc300		90		%
φ	Half angle			±60		٥
Vo	Open Circuit Voltage	$I_e = 0.5 \text{ mW/cm}^2$		300		mV
TC <sub>∨</sub>	Temperature Coefficient of I <sub>SC</sub>			0.38		%/K
TCo	Temperature Coefficient of Vo			-3.0		mV/K

# Type Specific Characteristics @ +25°C (all diodes of the array connected in parallel)

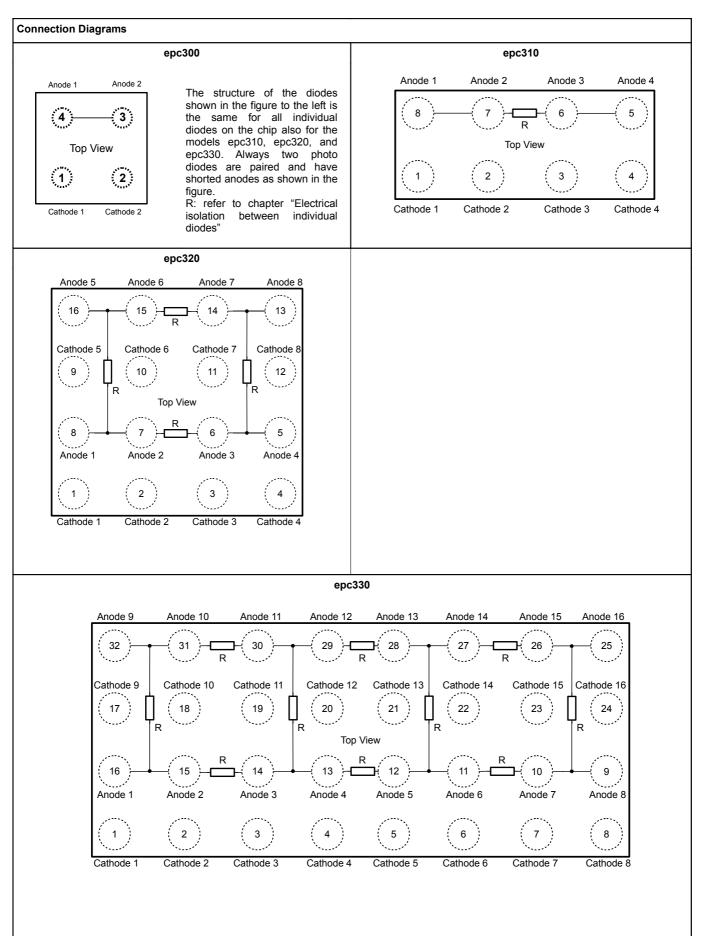
Symbol	Parameter		Conditions/Comments		Values		
				Min.	Тур.	Max.	
I <sub>P</sub>	Photo Current	per diode	$V_R = 5V$ , $I_e = 1 \text{ mW/cm}^2$ ,		2.5		μA
		ерс300	λ = 850 nm (NIR filter centered on 850nm)		5		
		epc310			10		
		epc320			20		
		epc330			40		
I <sub>R</sub>	Dark Current *	per diode	V <sub>R</sub> = 5 V, T <sub>A</sub> = 20°C		20	250	pА
		ерс300			40	500	
		epc310			80	1000	
		epc320			160	2000	
		epc330			320	4000	
I <sub>sc</sub>	Short-circuit Current	per diode	I <sub>e</sub> = 1 mW/cm <sup>2</sup>		2.5		μΑ
		ерс300			5		
		epc310			10		
		epc320			20		
		ерс330			40		

<sup>\*</sup> selected types available upon request



Symbol	Parameter		Conditions/Comments	Values			Units
				Min.	Тур.	Max.	
t <sub>r</sub>	Rise/Fall Time	all types	photo current measured at R <sub>L</sub> = 50 $\Omega$ , $\lambda$ = 850 nm, I <sub>P</sub> = 200 $\mu$ A				ns
			V <sub>R</sub> = +1.5 V		300		
			V <sub>R</sub> = +5.0 V		150		
			V <sub>R</sub> = +10.0 V		90		
Co	Capacitance	per diode	$V_R = +5V, f = 100kHz, E = 0$		5		pF
		ерс300			10		
		epc310			20		
		ерс320			40		
		ерс330			80		
NEP	Noise Equivalent Power	per diode	V <sub>R</sub> = 5 V		4.2x10 <sup>-15</sup>		W/√Hz
		ерс300			6.0x10 <sup>-15</sup>		
		epc310			8.4x10 <sup>-15</sup>		
		epc320			1.2x10 <sup>-14</sup>		
		ерс330			1.7x10 <sup>-14</sup>		
Ст	Cross Talk Suppression	epc320 epc330	between individual photo diodes on the same chip, if the voltage difference $V_{\text{diff}}$ is <100mV between individual diodes (cathodes)		50		dB

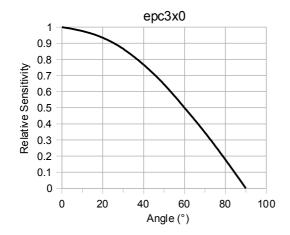




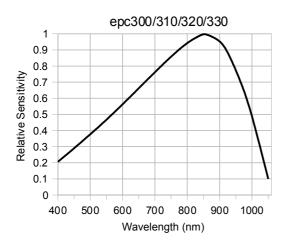


### **Other Parameters**

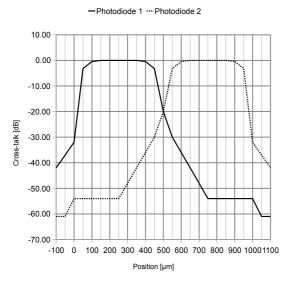
(typical values,  $T_{amb} = 25^{\circ}C$ ,  $V_{DD} = 5.0V$ ,  $I_{PD}=0mA$ )



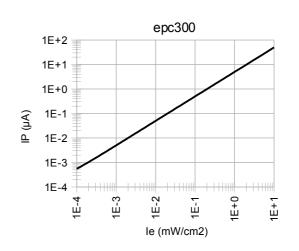
Relative sensitivity vs. illumination angle



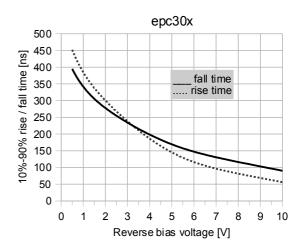
Relative spectral sensitivity



Cross-talk between a pair of photodiodes



Photocurrent  $I_P = f(I_e)$ ,  $V_R = 5 V$ ,  $\lambda = 850 nm$ 



Rise/fall time versus reverse bias voltage



# Application Information

#### **Light Barrier Application**

The following circuit uses an epc3xx photo diode with an epc13x PD amplifier chip. This circuit offers a very high AC photo current sensitivity and a tremendous DC backlight suppression.

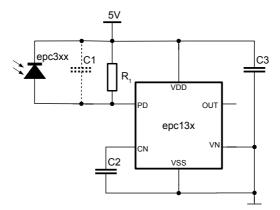


Figure 1: Typical schematic circuit using an epc13x PD amplifier

#### **Recommended Components Values**

R1: 27k (bias resistor). Sensitivity can be reduced by the reduction of this resistor.

C1: Usually not needed. May be up to 100 pF (refer to the epc13x data sheet).

C2: 33nF (DC input current filter capacitor)

C3: 100nF or more (power supply filter capacitor)

#### **Spectral Sensitivity**

This photo diode contains an anti-reflection coating on the photosensitive surface. Standard versions have no optical filter in order to allow applications from the near UV to the near IR range. However, optical filters deposited on the photosensitive surface are available upon request. The filter parameters can be adjusted in a wide range according to specific customer requirements.

### **Electrical Isolation between individual Diodes**

The individual diodes are located on a monolithic silicon chip. Thus, the electrical isolation between the individual diodes is not as good as with diodes on separate substrates. The substrate is conductive in x and y direction between all anodes, e.g. indicated in schematics by "R". In x direction between the anode pairs ca.  $20k\Omega$  is a typical value. They must not be used as resistor components.

### Design rules

On chip are the anodes metallic connect together by pairs. The user has to take care, that all anode pins are connected to the same voltage level (refer to above section).

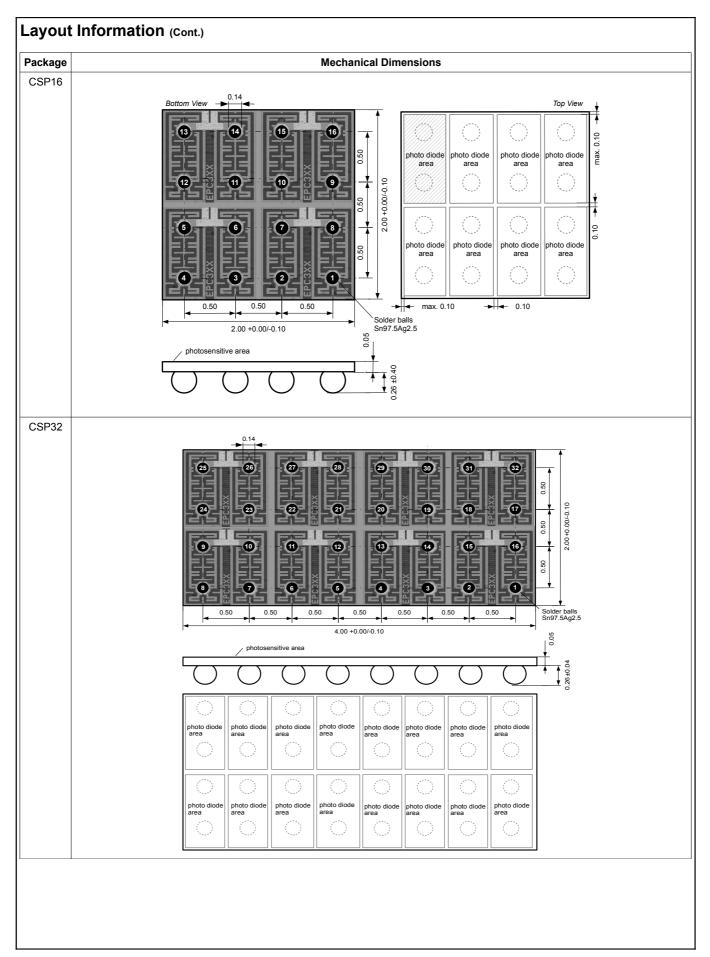
All pins of the diode array should be connected electrical-wise.

The biasing of the cathodes can be individual. Their voltage levels should be equal best match.



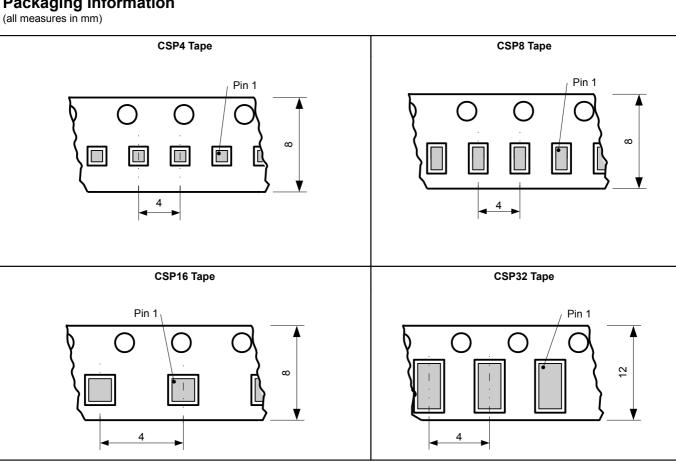
## **Layout Information** (all measures in mm, Package **Mechanical Dimensions Layout Recommendations** CSP4 max. 0.1524 Ø 0.30 1.00 +0.00/-0.10 photo diode photo diode area area 0.50 1.00 9 0.40 0.50 Solder balls Sn97.5Ag2.5 1.00 +0.00/-0.10 photosensitive area 0.50 1.00 no solder mask inside this area CSP8 max. 0.1524 Top View Ø 0.30 photo diode area 0.50 ı 0.50 2.00 ±0.00/-0.10 ı 0.50 ī 2.00 ī photo diode area 0.50 photo diode area т 0.50 Solder balls Sn97.5Ag2.5 0.50 1.00 ±0.00/-0.10 0.50 photosensitive area 1.00 0.26 ±0.04 no solder mask inside this area







# **Packaging Information**



### **Tape & Reel Information**

reels and individually packaged for shipment. General tape-and-reel specification data are available in a separate data sheet and indicate the tape sizes for various package types. Further tape-and-reel specifications can be found in the Electronic Industries Association (EIA) standard 481-1, 481-2, 481-3. The devices are mounted on embossed tape for automatic placement systems. The tape is wound on 178 mm (7 inch) or 330 mm (13 inch)

epc does not guarantee non-empty cavities. Thus, pick-and-place machines should check the presence of a chip during picking.

It is highly recommended to use underfill after assembly of the chips to the PCB.

# **Ordering Information**

Part Name	Package	RoHS compliance	Packaging Method		
epc300-CSP4	CSP4	Yes	Reel		
epc310-CSP8	CSP8	Yes	Reel		
epc320-CSP16	CSP16	Yes	Reel		
epc330-CSP32	CSP32	Yes	Reel		



#### **IMPORTANT NOTICE**

ESPROS Photonics AG and its subsidiaries (epc) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to epc's terms and conditions of sale supplied at the time of order acknowledgment.

epc warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with epc's standard warranty. Testing and other quality control techniques are used to the extent epc deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

epc assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using epc components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

epc does not warrant or represent that any license, either express or implied, is granted under any epc patent right, copyright, mask work right, or other epc intellectual property right relating to any combination, machine, or process in which epc products or services are used. Information published by epc regarding third-party products or services does not constitute a license from epc to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from epc under the patents or other intellectual property of epc.

Resale of epc products or services with statements different from or beyond the parameters stated by epc for that product or service voids all express and any implied warranties for the associated epc product or service. epc is not responsible or liable for any such statements.

epc products are not authorized for use in safety-critical applications (such as life support) where a failure of the epc product would reasonably be expected to cause severe personal injury or death, unless officers of the parties have executed an agreement specifically governing such use. Buyers represent that they have all necessary expertise in the safety and regulatory ramifications of their applications, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of epc products in such safety-critical applications, notwithstanding any applications-related information or support that may be provided by epc. Further, Buyers must fully indemnify epc and its representatives against any damages arising out of the use of epc products in such safety-critical applications.

epc products are neither designed nor intended for use in military/aerospace applications or environments unless the epc products are specifically designated by epc as military-grade or "enhanced plastic." Only products designated by epc as military-grade meet military specifications. Buyers acknowledge and agree that any such use of epc products which epc has not designated as military-grade is solely at the Buyer's risk, and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

epc products are neither designed nor intended for use in automotive applications or environments unless the specific epc products are designated by epc as compliant with ISO/TS 16949 requirements. Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, epc will not be responsible for any failure to meet such requirements.